

What is claimed is:

1. An active matrix substrate, comprising:
electrode wires constituted by scanning electrodes
and signal electrodes that are arranged in a lattice;
an insulating film provided at least on the
electrode wires so as to have openings in predetermined
areas at least either on the scanning electrodes or on
the signal electrodes; and
a metal layer stacked on the electrodes in the
openings.
2. The active matrix substrate as defined in claim 1,
wherein:
the metal layer includes at least one kind of metal
film selected from the group consisting of a nickel film,
a copper film, and a gold film.
3. The active matrix substrate as defined in claim 1,
wherein:
the metal layer includes a plurality of layers.
4. The active matrix substrate as defined in claim 1,
wherein:
at least either the scanning electrodes or the

signal electrodes are fabricated from a transparent conducting oxide film.

5. The active matrix substrate as defined in claim 1, wherein:

the insulating film is made of SiNx.

6. The active matrix substrate as defined in claim 1, wherein:

the metal layer is formed by wet plating.

7. A display device, comprising:

an active matrix substrate; and

an electro-optical medium driven by the active matrix substrate,

the active matrix substrate including: electrode wires constituted by scanning electrodes and signal electrodes that are arranged in a lattice; an insulating film provided at least on the electrode wires so as to have openings in predetermined areas at least either on the scanning electrodes or on the signal electrodes; and a metal layer stacked on the electrodes in the openings.

8. The display device as defined in claim 7, wherein:

the metal layer includes at least one kind of metal film selected from the group consisting of a nickel film, a copper film, and a gold film.

9. The display device as defined in claim 7,
wherein:
the metal layer includes a plurality of layers.

10. The display device as defined in claim 7,
wherein:
at least either the scanning electrodes or the signal electrodes are fabricated from a transparent conducting oxide film.

11. The display device as defined in claim 7,
wherein:
the insulating film is made of SiN_x .

12. The display device as defined in claim 7,
wherein:
the electro-optical medium is a liquid crystal.

13. The display device as defined in claim 7,
wherein:
the metal layer is formed by wet plating.

14. An image-capturing device, comprising:

an active matrix substrate; and

a photoconductor of which electric charge is read by the active matrix substrate

the active matrix substrate including: electrode wires constituted by scanning electrodes and signal electrodes that are arranged in a lattice; an insulating film provided at least on the electrode wires so as to have openings in predetermined areas at least either on the scanning electrodes or on the signal electrodes; and a metal layer stacked on the electrodes in the openings.

15. The image-capturing device as defined in claim 14, wherein:

the metal layer includes at least one kind of metal film selected from the group consisting of a nickel film, a copper film, and a gold film.

16. The image-capturing device as defined in claim 14, wherein:

the metal layer includes a plurality of layers.

17. The image-capturing device as defined in claim 14, wherein:

at least either the scanning electrodes or the

signal electrodes are fabricated from a transparent conducting oxide film.

18. The image-capturing device as defined in claim 14,
wherein:

the insulating film is made of SiNx .

19. The image-capturing device as defined in claim 14,
wherein:

the photoconductor is made of amorphous selenium.

20. The image-capturing device as defined in claim 14,
further comprising:

a luminescent layer.

21. The image-capturing device as defined in claim 14,
wherein:

the metal layer is formed by wet plating.

22. A method of manufacturing an active matrix substrate, comprising the steps of:

(a) forming scanning electrodes and signal electrodes, for acting as electrode wires, arranged in a lattice on a substrate;

(b) forming an insulating film at least on the

electrode wires so as to have openings in predetermined areas at least either on the scanning electrodes or on the signal electrodes; and

(c) forming a metal layer selectively in the openings on the electrodes.

23. The method of manufacturing an active matrix substrate as defined in claim 22,

wherein:

the insulating film is made of SiN_x .

24. The method of manufacturing an active matrix substrate as defined in claim 22,

wherein:

the insulating film is made of SiN_x , and the metal layer is made of copper.

25. The method of manufacturing an active matrix substrate as defined in claim 22,

wherein:

the metal layer is formed by electric plating.

26. The method of manufacturing an active matrix substrate as defined in claim 22,

wherein:

the metal layer is formed by electroless plating.